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Attorney Docket No.: 01CON211P

In the Claims:

Claim 1 (currently amended): An integrated circuit chip comprising:

a first interconnect metal layer;

a first intermetallic dielectric layer situated over said first interconnect metal layer;

a metal resistor situated over said first intermetallic dielectric layer, said metal resistor ~~not~~ being only connected to ~~said first~~ a second interconnect metal layer;

a dielectric cap layer patterned on said metal resistor;

a second intermetallic dielectric layer formed over said dielectric cap layer and said metal resistor;

a said second interconnect metal layer over said second intermetallic dielectric layer, wherein said first and second interconnect metal layers are adjacent to each other and wherein said metal resistor is situated between said first and second interconnect metal layers;

a first intermediate via connected to a first terminal of said metal resistor, said first intermediate via being further connected to a first metal segment patterned in said second interconnect metal layer;

a second intermediate via connected to a second terminal of said metal resistor, said second intermediate via being further connected to a second metal segment patterned in said second interconnect metal layer.

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Claim 2 (original): The integrated circuit chip of claim 1 wherein said metal resistor is selected from the group consisting of titanium nitride and tantalum nitride.

Claim 3 (original): The integrated circuit chip of claim 1 wherein said first interconnect metal layer comprises aluminum.

Claim 4 (original): The integrated circuit chip of claim 1 wherein said first intermetallic dielectric layer comprises HDPCVD silicon dioxide.

Claim 5 (original): The integrated circuit chip of claim 1 wherein said second intermetallic dielectric layer comprises undoped silica glass.

Claim 6 (canceled).

Claim 7 (previously presented): The integrated circuit chip of claim 1 wherein said dielectric cap layer comprises silicon nitride.

Claim 8 (original): The integrated circuit chip of claim 1 further comprising an oxide cap layer situated between said metal resistor and said first intermetallic dielectric layer.

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Claim 9 (original): The integrated circuit chip of claim 8 wherein said oxide cap layer comprises PECVD silicon dioxide.

Claim 10 (currently amended): An integrated circuit chip comprising:

- a first interconnect metal layer;
- a first intermetallic dielectric layer situated over said first interconnect metal layer;
- a metal resistor situated over said first intermetallic dielectric layer, said metal resistor ~~not~~ being only connected to ~~said first~~ a second interconnect metal layer;
- a dielectric cap layer patterned on said metal resistor;
- a second intermetallic dielectric layer formed over said dielectric cap layer and said metal resistor;
- a said second interconnect metal layer over said second intermetallic dielectric layer, wherein said first and second interconnect metal layers are adjacent to each other and wherein said metal resistor is situated between said first and second interconnect metal layers;
- a first intermediate via connected to a first terminal of said metal resistor and said second interconnect metal layer;
- a second intermediate via connected to a second terminal of said metal resistor and said second interconnect metal layer.

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Claim 11 (original): The integrated circuit chip of claim 10 wherein said metal resistor is selected from the group consisting of titanium nitride and tantalum nitride.

Claim 12 (original): The integrated circuit chip of claim 10 wherein said first intermetallic dielectric layer comprises HDPCVD silicon dioxide.

Claim 13 (original): The integrated circuit chip of claim 10 wherein said second intermetallic dielectric layer comprises undoped silica glass.

Claim 14 (canceled).

Claim 15 (previously presented): The integrated circuit chip of claim 10 wherein said dielectric cap layer comprises silicon nitride.

Claim 16 (original): The integrated circuit chip of claim 10 wherein said first interconnect metal layer comprises aluminum.

Claim 17 (original): The integrated circuit chip of claim 10 further comprising an oxide cap layer situated between said metal resistor and said first intermetallic dielectric layer.

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Claim 18 (original): The integrated circuit chip of claim 17 wherein said oxide cap layer comprises PECVD silicon dioxide.

Claims 19-27 (canceled).

Claim 28 (previously presented): The integrated circuit chip of claim 1 wherein said metal resistor is not connected from below.

Claim 29 (previously presented): The integrated circuit chip of claim 1 wherein the thickness of said metal resistor is approximately 100.0 Angstroms to 1500.0 Angstroms.

Claim 30 (previously presented): The integrated circuit chip of claim 10 wherein said metal resistor is not connected from below.

Claim 31 (previously presented): The integrated circuit chip of claim 10 wherein the thickness of said metal resistor is approximately 100.0 Angstroms to 1500.0 Angstroms.

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